

Please replace the abstract with the following amended abstract:

A method for manufacturing a semiconductor device suppresses ~~capable of suppressing the~~ electric charge ~~[[as]]~~ charged up in a semiconductor layer of an SOI substrate at the time of ~~[[the]]~~ ion implantation, ~~[[thus]]~~ preventing a BOX layer and a gate oxide from being damaged. ~~By means of LOCOS method, a~~ A field oxide film ~~[[20]]~~ is formed on a semiconductor layer ~~18 which is formed on a BOX layer 16 making up of the SOI wafer 12 of a semiconductor device 100.~~ A conductive layer ~~[[102]]~~ is formed on the field oxide film ~~[[20]]~~ and a gate oxide film ~~[[26]]~~ as well. The conductive layer ~~[[102]]~~ made of amorphous carbon is formed by ~~means of the sputtering method~~ and has a thickness of 5nm to 10nm. B+ ~~[[24]]~~ is implanted in the interface between the semiconductor layer ~~[[18]]~~ and the gate oxide film ~~[[22]]~~ by ~~means of an~~ intermediate dose ion implanter. The electric charge ~~[[38]]~~ generated in the semiconductor layer ~~[[18]]~~ at the time of ~~[[the]]~~ ion implantation results in ~~[[the]]~~ FN current, which is removed through the gate oxide film ~~[[22]]~~ and the conductive layer ~~102 as well. After removing the conductive layer 102, a gate electrode 26 is formed on the gate oxide film 22[.]~~